

isc Silicon NPN Power Transistor

2SD1047E

DESCRIPTION

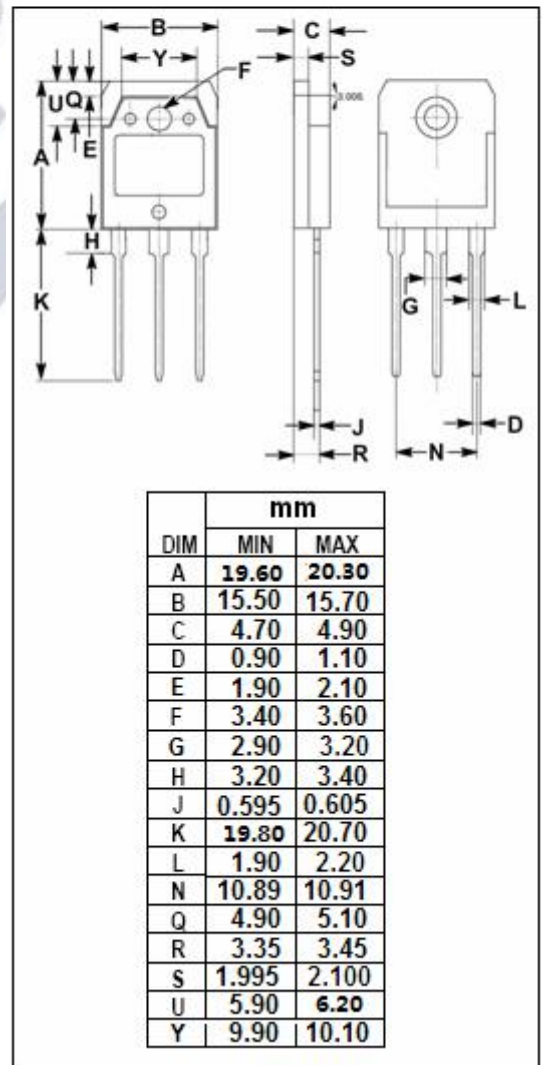
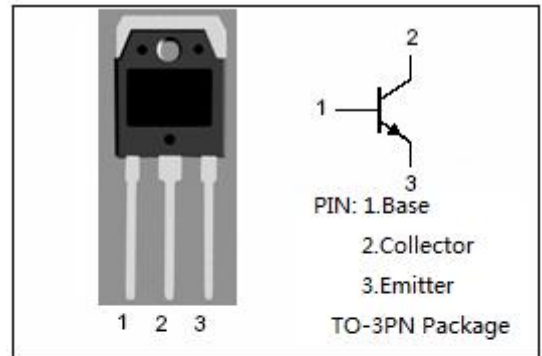
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 140V(\text{Min})$
- Good Linearity of h_{FE}
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SB817E
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	140	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	12	A
I_{CP}	Collector Current-Pulse	15	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	100	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-40~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=30\text{mA}$; $R_{BE}=\infty$	140			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=5\text{mA}$; $I_E=0$	160			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=5\text{mA}$; $I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5.0\text{A}$; $I_B=0.5\text{A}$		0.6	2.5	V
$V_{BE(on)}$	Base -Emitter On Voltage	$I_C=1\text{A}$; $V_{CE}=5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}$; $I_E=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4\text{V}$; $I_C=0$			100	μA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}$; $V_{CE}=5\text{V}$	100		200	
h_{FE-2}	DC Current Gain	$I_C=6\text{A}$; $V_{CE}=5\text{V}$	20			
C_{OB}	Output Capacitance	$I_E=0$; $V_{CB}=10\text{V}$; $f_{test}=1.0\text{MHz}$		210		pF
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}$; $V_{CE}=5\text{V}$		15		MHz

Switching times

t_{on}	Turn-on Time	$I_C=1\text{A}$, $R_L=20\Omega$, $I_{B1}=I_{B2}=0.1\text{A}$, $V_{CC}=20\text{V}$		0.26		μs
t_{stg}	Storage Time			6.88		μs
t_f	Fall Time			0.68		μs